

**Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Original) A high voltage semiconductor device, comprising:  
a high concentration collector area of a first conductive type;  
a low concentration collector area of a first conductive type formed on the high concentration collector area;  
a base area of a second conductive type formed on the low concentration collector area and having a trench which penetrates the low concentration collector area in a vertical direction at a junction termination;  
a high concentration emitter area of a first conductive type formed on a predetermined upper surface of the base area; and  
an emitter electrode, a base electrode, and a collector electrode isolated from one another and connected to the emitter area, the base area, and the collector area, respectively, wherein the depth of the trench is 50-150  $\mu\text{m}$ .
2. (Original) The high voltage semiconductor device of claim 1, further comprising an oxide layer which fills the trench.
3. (New) The high voltage semiconductor device of claim 1, wherein the width of the trench is about 1/10 the depth of the trench.